

P-Channel Enhancement Mode MOSFET General Purpose Amplifier

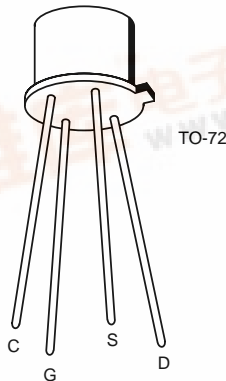


IT1700

FEATURES

- Low ON-Resistance
- High Gain
- Low Noise Voltage
- High Input Impedance
- Low Leakage

PIN CONFIGURATION



1503

ABSOLUTE MAXIMUM RATINGS

($T_A = 25^\circ\text{C}$ unless otherwise specified)

Drain-Source and Gate-Source Voltage -40V
Peak Gate-Source Voltage (Note 1) $\pm 125\text{V}$
Drain Current 50mA
Storage Temperature -65°C to $+200^\circ\text{C}$
Operating Temperature Range -55°C to $+150^\circ\text{C}$
Lead Temperature (Soldering, 10sec) $+300^\circ\text{C}$
Power Dissipation 375mW
Derate above 25°C $3\text{mW}/^\circ\text{C}$

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ORDERING INFORMATION

Part	Package	Temperature Range
IT1700	Hermetic TO-72	-55°C to $+150^\circ\text{C}$
XIT1700	Sorted Chips in Carriers	-55°C to $+150^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ and $V_{BS} = 0$ unless otherwise specified)

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
BV_{DSS}	Drain to Source Breakdown Voltage	-40		V	$V_{GS} = 0, I_D = -10\mu\text{A}$
BV_{SDS}	Source to Drain Breakdown Voltage	-40		V	$V_{GS} = 0, I_D = -10\mu\text{A}$
I_{GSS}	Gate Leakage Current	(See note 2)			
I_{DSS}	Drain to Source Leakage Current		200	pA	$V_{GS} = 0, V_{DS} = -20\text{V}$
$I_{DSS}(150^\circ\text{C})$	Drain to Source Leakage Current		0.4	μA	
I_{SDS}	Source to Drain Leakage Current		400	pA	
$I_{SDS}(150^\circ\text{C})$	Source to Drain Leakage Current		0.8	μA	
$V_{GS(th)}$	Gate Threshold Voltage	-2	-5	V	$V_{GS} = V_{DS}, I_D = -10\mu\text{A}$
$r_{DS(on)}$	Static Drain to Source "on" Resistance		400	ohms	$V_{GS} = -10\text{V}, V_{DS} = 0$
$I_{DS(on)}$	Drain to Source "on" Current	2		mA	$V_{GS} = -10\text{V}, V_{DS} = -15\text{V}$
g_{fs}	Forward Transconductance Common Source	2000	4000	μS	$V_{DS} = -15\text{V}, I_D = -10\text{mA}, f = 1\text{kHz}$
C_{iss}	Small Signal, Short Circuit, Common Source, Input Capacitance		5	pF	$V_{DS} = -15\text{V}, I_D = -10\text{mA}$ $f = 1\text{MHz}$ (Note 3)
C_{rss}	Small Signal, Short Circuit, Common Source, Reverse Transfer Capacitance		1.2	pF	$V_{DG} = -15\text{V}, I_D = 0$ $f = 1\text{MHz}$ (Note 3)
C_{oss}	Small Signal, Short Circuit, Common Source, Output Capacitance		3.5	pF	$V_{DS} = -15\text{V}, I_D = -10\text{mA}$ $f = 1\text{MHz}$ (Note 3)

- NOTES:**
1. Device must not be tested at $\pm 125\text{V}$ more than once nor longer than 300ms.
 2. Actual gate current is immeasurable. Package suppliers are required to guarantee a package leakage of $< 10\text{pA}$.
External package leakage is the dominant mode which is sensitive to both transient and storage environment, which cannot be guaranteed.
 3. For design reference only, not 100% tested.